

# MOS FIELD EFFECT TRANSISTOR

## 2SJ449

### SWITCHING P-CHANNEL MOS FET INDUSTRIAL USE

#### DESCRIPTION

The 2SJ449 is P-Channel MOS Field Effect Transistor designed for high voltage switching applications.

#### FEATURES

- Low On-Resistance  
 $R_{DS(on)} = 0.8 \Omega \text{ MAX. (@ } V_{GS} = -10 \text{ V, } I_D = -3.0 \text{ A)}$
- Low  $C_{iss}$   $C_{iss} = 1040 \text{ pF TYP.}$
- High Avalanche Capability Ratings
- Isolated TO-220 Package

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

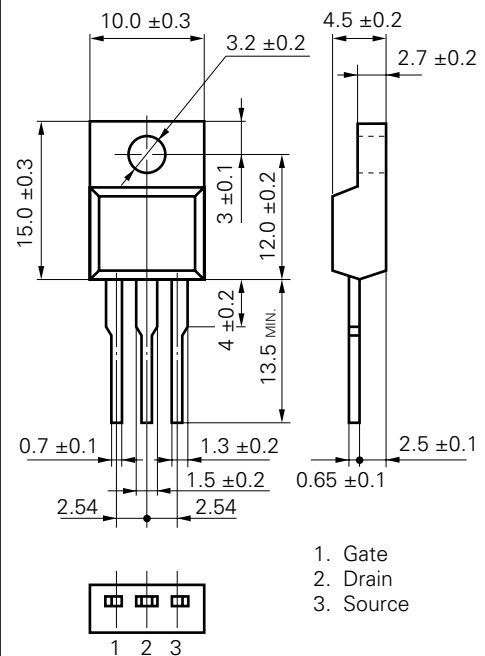
Drain to Source Voltage	$V_{DSS}$	-250	V
Gate to Source Voltage	$V_{GSS}$	$\mp 30$	V
Drain Current (DC)	$I_{D(DC)}$	$\mp 6.0$	A
Drain Current (pulse)*	$I_{D(pulse)}$	$\mp 24$	A
Total Power Dissipation ( $T_c = 25^\circ\text{C}$ )	$P_{T1}$	35	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_{T2}$	2.0	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Single Avalanche Current**	$I_{AS}$	-6.0	A
Single Avalanche Energy**	$E_{AS}$	180	mJ

\*  $PW \leq 10 \mu\text{s}$ , Duty Cycle  $\leq 1\%$

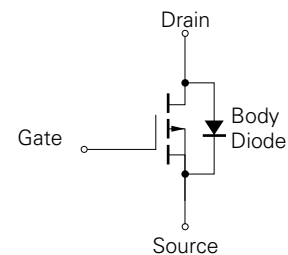
\*\* Starting  $T_{ch} = 25^\circ\text{C}$ ,  $R_G = 25 \Omega$ ,  $V_{GS} = -20 \text{ V} \rightarrow 0$

#### PACKAGE DIMENSIONS

(in millimeters)



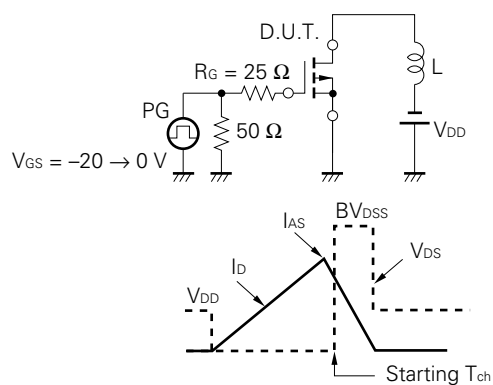
#### MP-45F (ISOLATED TO-220)



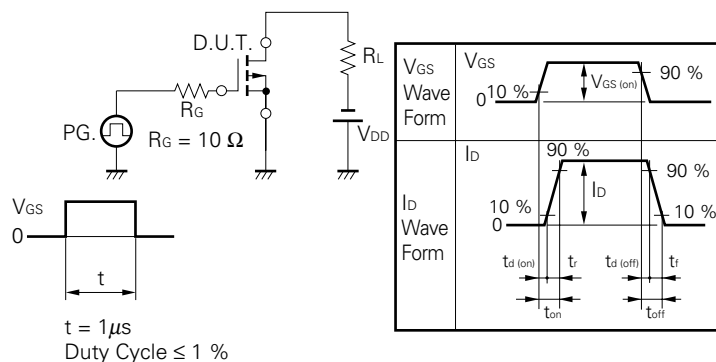
ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-Resistance	R <sub>DS(on)</sub>		0.55	0.8	Ω	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -3.0 A
Gate to Source Cutoff Voltage	V <sub>GS(off)</sub>	-4.0	-4.8	-5.5	V	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA
Forward Transfer Admittance	y <sub>fs</sub>	2.0	3.5		S	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -3.0 A
Drain Leakage Current	I <sub>DSS</sub>			-100	μA	V <sub>DS</sub> = -250 V, V <sub>GS</sub> = 0
Gate to Source Leakage Current	I <sub>GSS</sub>			±100	nA	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0
Input Capacitance	C <sub>iss</sub>		1040		pF	V <sub>DS</sub> = -10 V V <sub>GS</sub> = 0 f = 1 MHz
Output Capacitance	C <sub>oss</sub>		360		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		70		pF	
Turn-On Delay Time	t <sub>d(on)</sub>		24		ns	
Rise Time	t <sub>r</sub>		16		ns	I <sub>D</sub> = -3.0 A V <sub>GS(on)</sub> = -10 V V <sub>DD</sub> = -125 V R <sub>G</sub> = 10 Ω, R <sub>L</sub> = 42 Ω
Turn-Off Delay Time	t <sub>d(off)</sub>		47		ns	
Fall Time	t <sub>f</sub>		14		ns	
Total Gate Charge	Q <sub>G</sub>		23.1		nC	I <sub>D</sub> = -6.0 A V <sub>DD</sub> = -200 V V <sub>GS</sub> = -10 V
Gate to Source Charge	Q <sub>GS</sub>		7.1		nC	
Gate to Drain Charge	Q <sub>GD</sub>		12.9		nC	
Body Diode Forward Voltage	V <sub>F(S-D)</sub>		0.92		V	I <sub>F</sub> = -6.0 A, V <sub>GS</sub> = 0
Reverse Recovery Time	t <sub>rr</sub>		155		ns	I <sub>F</sub> = -6.0 A, V <sub>GS</sub> = 0 di/dt = 50 A/μs
Reverse Recovery Charge	Q <sub>rr</sub>		930		nC	

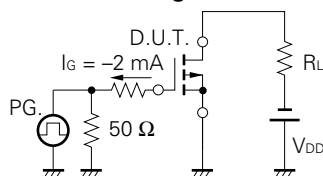
Test Circuit 1 Avalanche Capability



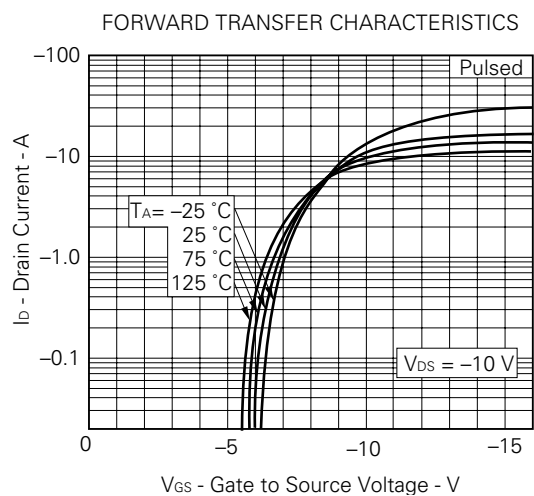
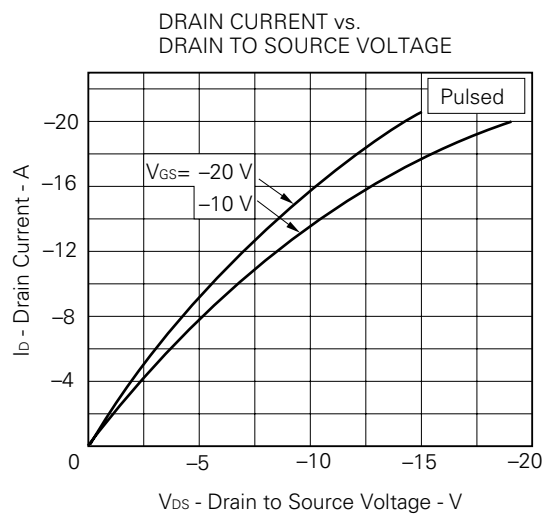
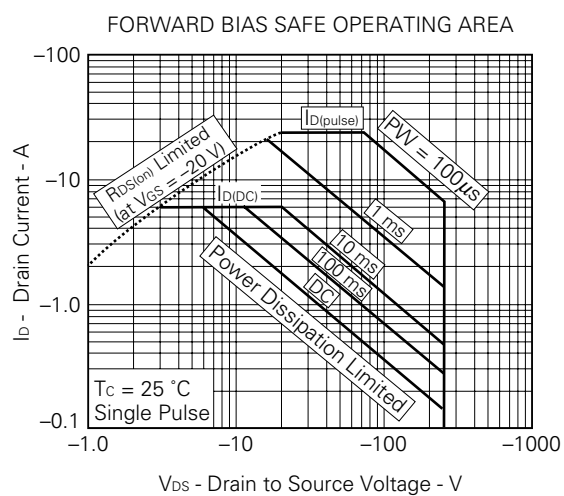
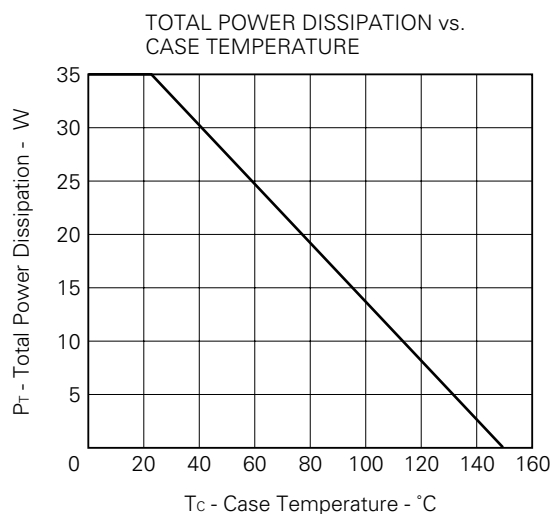
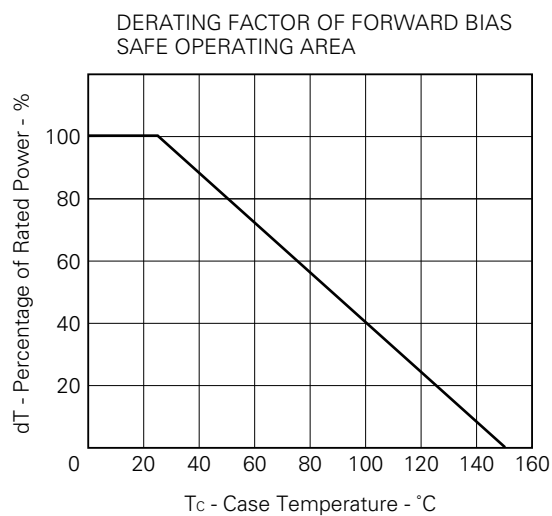
Test Circuit 2 Switching Time



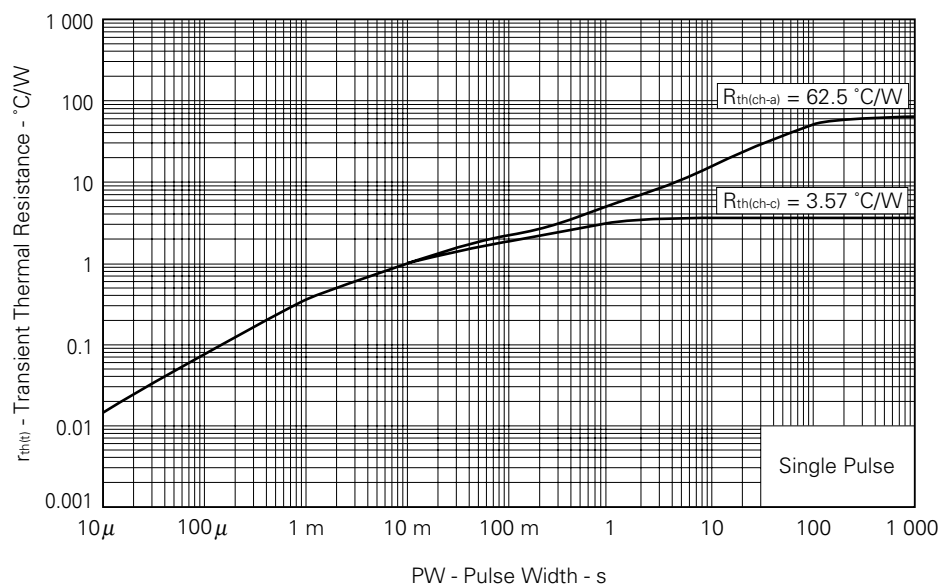
Test Circuit 3 Gate Charge



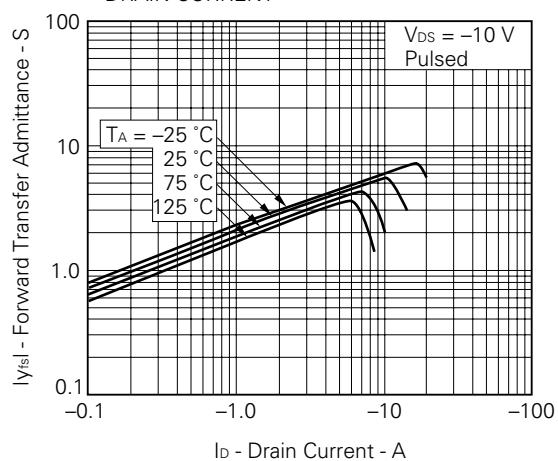
The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

TYPICAL CHARACTERISTICS ( $T_A = 25\text{ }^{\circ}\text{C}$ )

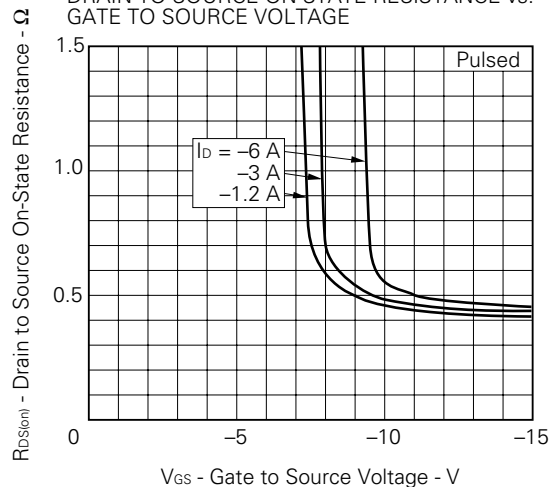
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



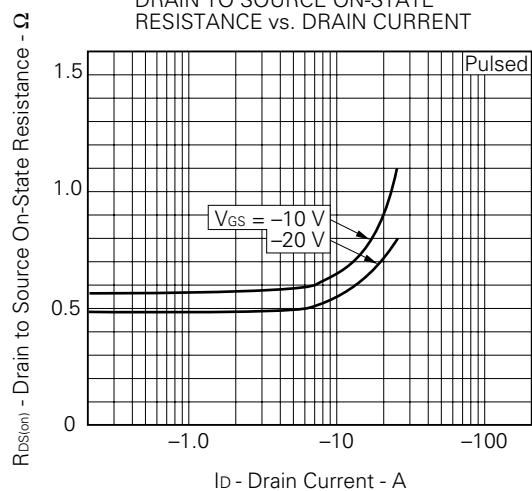
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



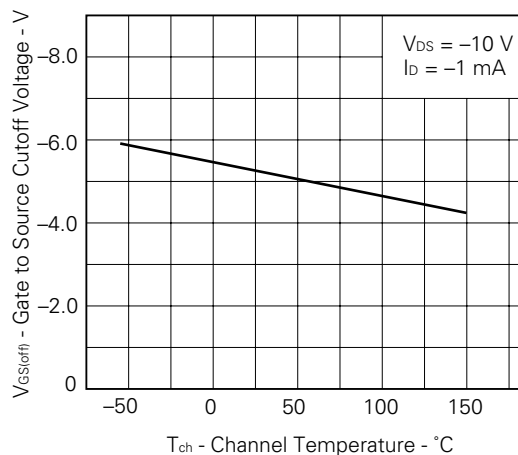
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



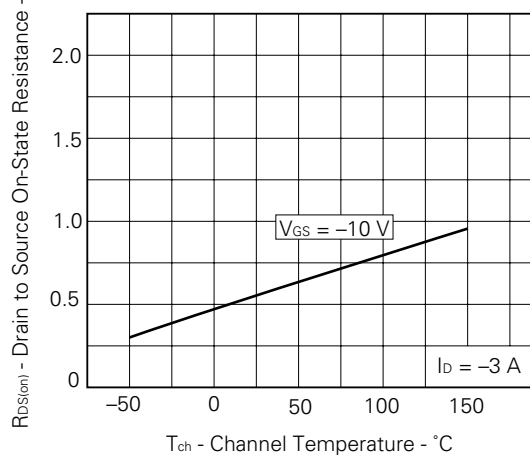
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



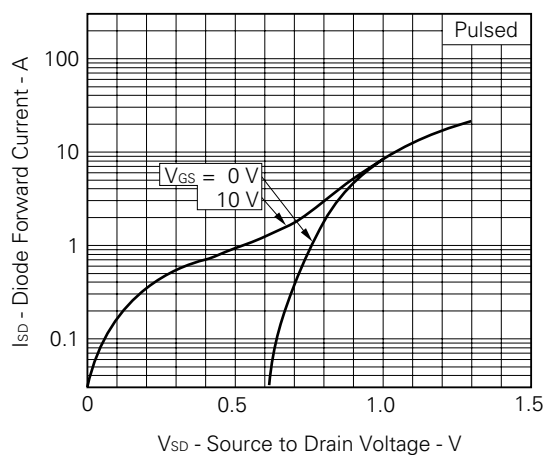
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



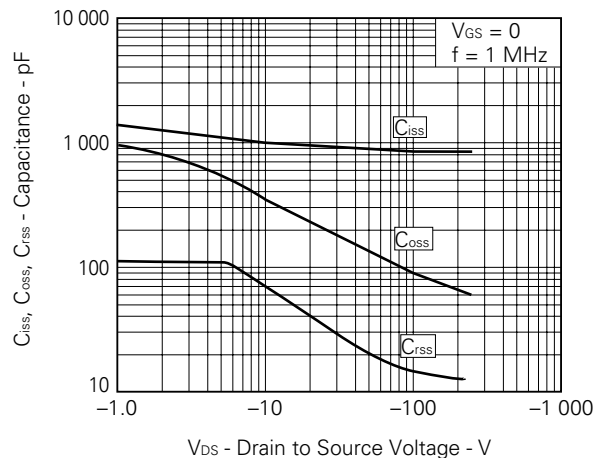
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



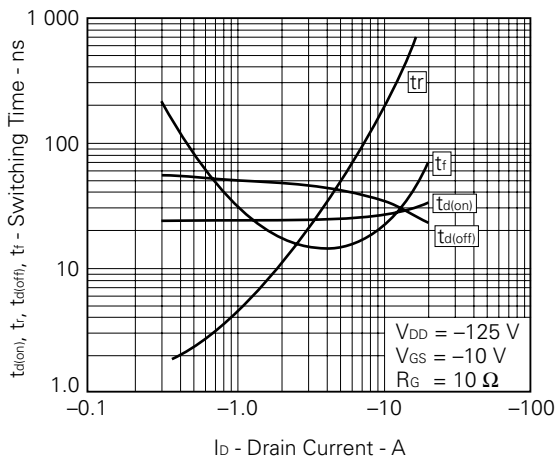
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



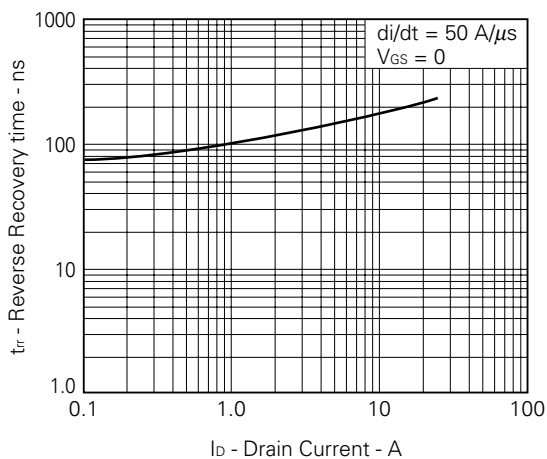
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



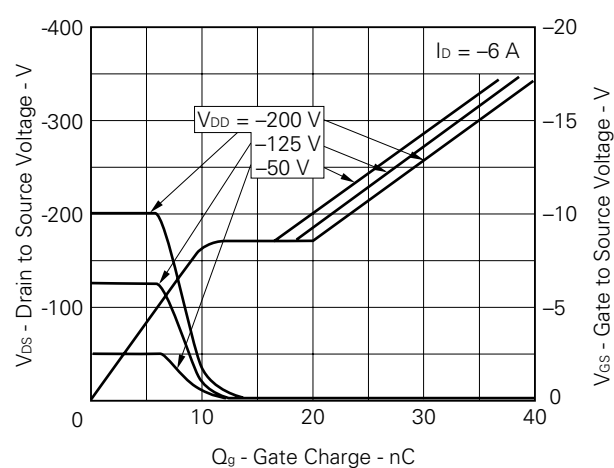
SWITCHING CHARACTERISTICS

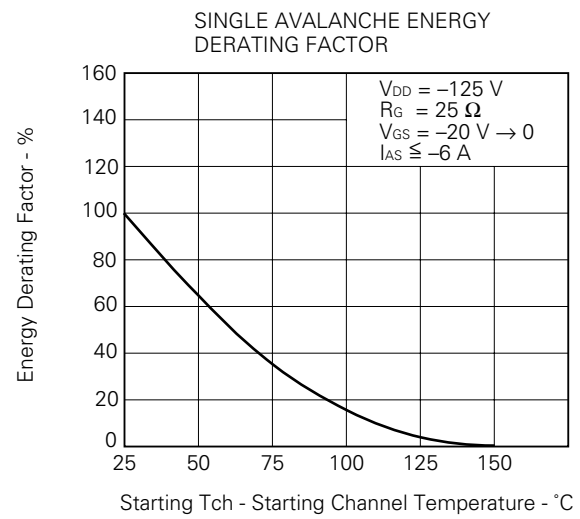
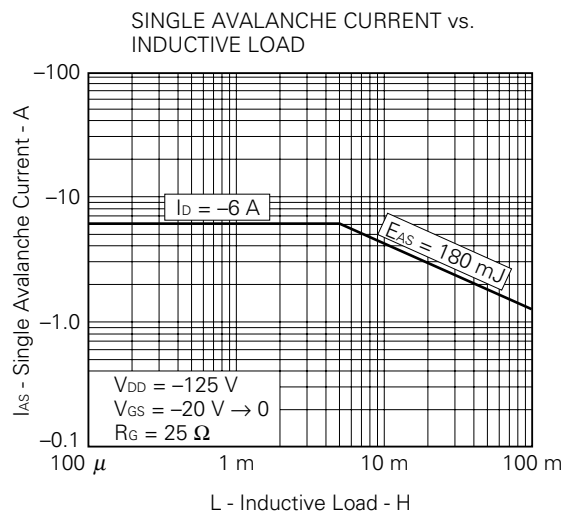


REVERSE RECOVERY TIME vs. DRAIN CURRENT



DYNAMIC INPUT/OUTPUT CHARACTERISTICS





## REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134
Power MOS FET features and application switching power supply.	TEA-1034
Application circuits using Power MOS FET.	TEA-1035
Safe operating area of Power MOS FET.	TEA-1037

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device is actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

[MEMO]

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Anti-radioactive design is not implemented in this product.